

2SD2655

Silicon NPN Epitaxial Planer
Low Frequency Power Amplifier

HITACHI

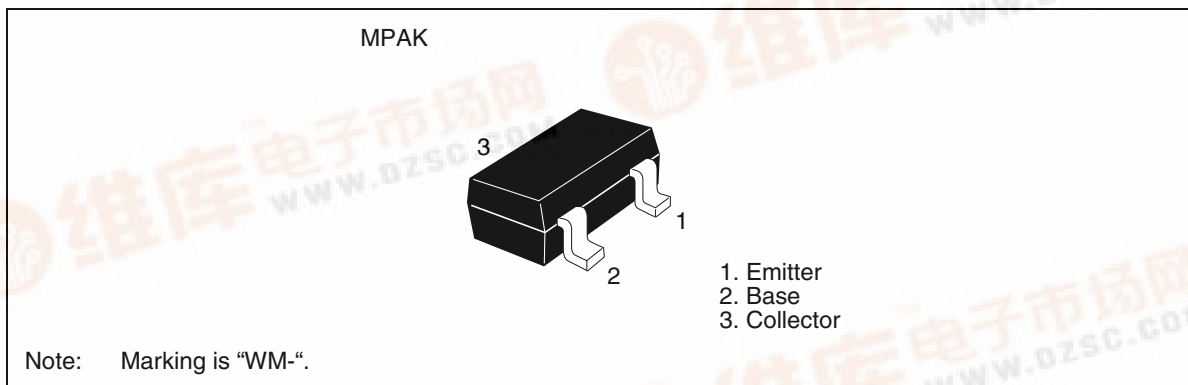
ADE-208-1388A (Z)

Rev.1
Jun. 2001

Features

- Small size package: MPAK (SC-59A)
- Large Maximum current: $I_C = 1 \text{ A}$
- Low collector to emitter saturation voltage: $V_{CE(sat)} = 0.3 \text{ V max. (at } I_C/I_B = 0.5 \text{ A}/0.05 \text{ A)}$
- High power dissipation: $P_C = 800 \text{ mW}$ (when using alumina ceramic board (25 x 60 x 0.7 mm))
- Complementary pair with 2SB1691

Outline



2SD2655

Absolute Maximum Ratings

($T_a = 25\text{ }^\circ\text{C}$)

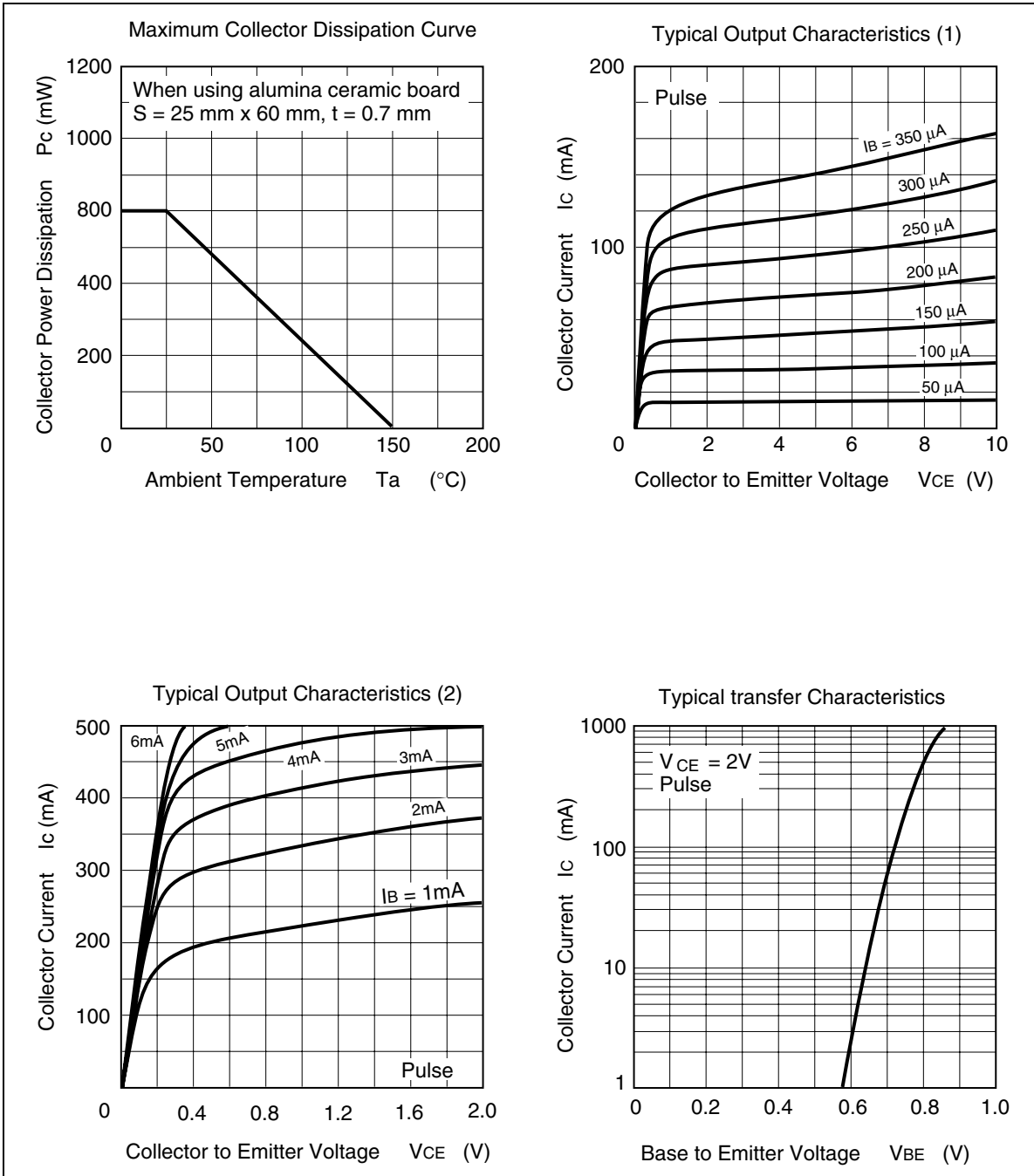
Item	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	1	A
Collector peak current	$i_c(\text{peak})$	2	A
Collector power dissipation	P_C	800*	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

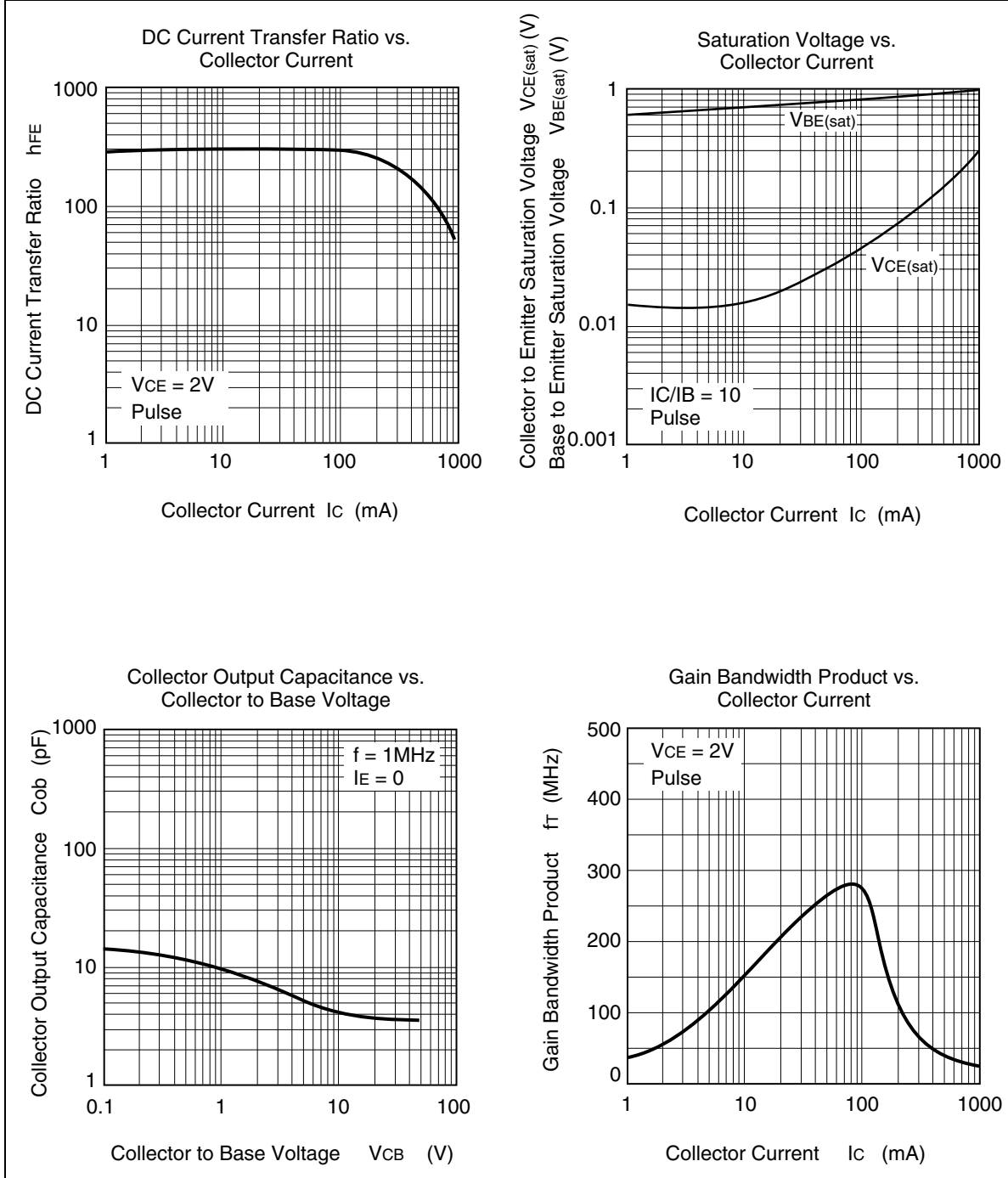
Note: *When using alumina ceramic board (25 x 60 x 0.7 mm)

Electrical Characteristics

($T_a = 25\text{ }^\circ\text{C}$)

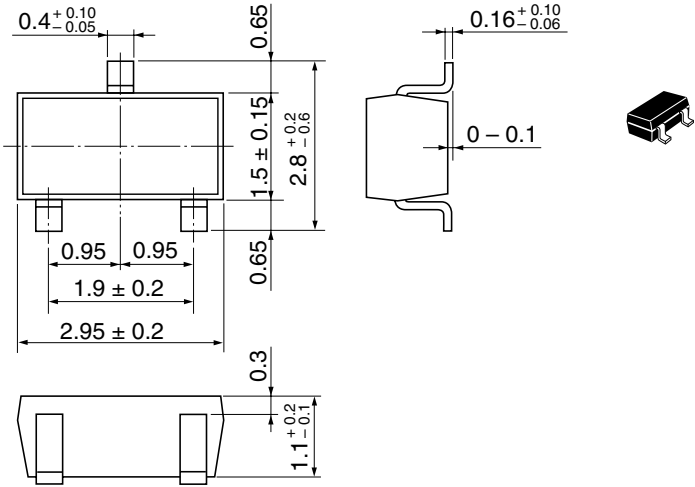
Item	Symbol	Min	Typ	Max	Unit	Test Condition
Collector to base breakdown voltage	$V_{(BR)CBO}$	60	—	—	V	$I_C = 10\text{ }\mu\text{A}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	50	—	—	V	$I_C = 1\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 10\text{ }\mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	100	nA	$V_{CB} = 50\text{ V}$, $I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	100	nA	$V_{EB} = 5\text{ V}$, $I_C = 0$
DC current transfer ratio	h_{FE}	200	—	500	—	$V_{CE} = 2\text{ V}$, $I_C = 0.1\text{ A}$
Collector to emitter saturation voltage	$V_{CE(\text{sat})}$	—	0.16	0.3	V	$I_C = 0.5\text{ A}$, $I_B = 0.05\text{ A}$, Pulse test
Base to emitter saturation voltage	$V_{BE(\text{sat})}$	—	0.91	1.2	V	$I_C = 0.5\text{ A}$, $I_B = 0.05\text{ A}$, Pulse test
Gain bandwidth product	f_T	—	280	—	MHz	$V_{CE} = 2\text{ V}$, $I_C = 0.1\text{ A}$
Collector output capacitance	C_{ob}	—	4.2	—	pF	$V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$





Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	MPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.011 g

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